

GANPAT UNIVERSITY

B. Tech. Semester IIIrd (EC) Electronics and Communication Engineering

Regular Examination November – December 2013

2EC302 - ELECTRONIC DEVICES AND CIRCUITS

Time: 3 Hours

Total Marks: 70

Instruction:

1. Attempt all questions.
2. Answers to the two sections must be written in separate answer books.
3. Figures to the right indicate full marks.
4. Assume suitable data, if necessary.

Section - I

- Que. – 1** (A) Define h-parameter of a transistor. Draw the equivalent circuit of a transistor with h-parameters. Derive the general expressions for current gain, voltage gain, input impedance, output impedance for a transistor amplifier circuit using h-parameters. **8**
- (B) Define active, saturation and cutoff regions in a transistor. Sketch a family of Common Emitter output characteristics for a transistor. **4**
- OR**
- Que. – 1** (A) Explain Miller's theorem. Also derive expressions for Miller effect input and output capacitances. **6**
- (B) For the circuit shown in figure. 1, draw the dc load line and plot the Q point. Sketch the Q point when β changes from 100 to 150 and 100 to 50. Show that Q point is sensitive to variation in β . **6**
- Que. – 2** (A) Define stability factors with respect to transistor biasing. State the factors affecting the stability. **4**
- (B) Write short note on phototransistor. **4**
- (C) Draw three basic configurations of NPN transistor. **3**
- OR**
- Que. – 2** (A) For the amplifier circuit shown in figure. 2, draw ac equivalent circuit using h-parameter model and r-parameter model. Derive expressions for input impedance, output impedance for given circuit using any one of the small signal models. **6**
- (B) What is the effect of emitter bypass capacitor on low frequency response of an amplifier? Explain the effect of parasitic capacitance and wiring capacitance on high frequency response of a BJT amplifier. **5**
- Que. – 3** (A) Draw and explain Emitter bias circuit. Derive expressions for d.c. voltages and currents in the circuit. Find I_C and V_{CE} for given $R_B = 220\text{ K}\Omega$, $R_C = R_E = 1\text{ K}\Omega$, $V_{CC} = 10\text{ V}$, $\beta = 100$. **7**
- (B) Define: Bandwidth of an amplifier, 3-dB frequency, AC Beta (β_{ac}). **3**
- (C) Why biasing is required? Explain in brief. **2**

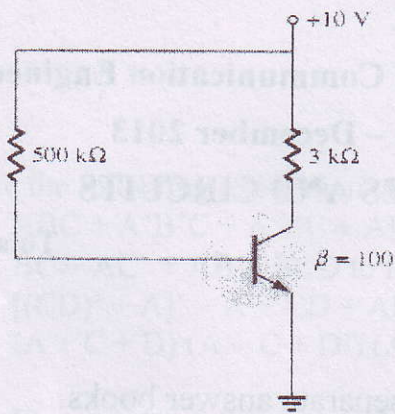


Figure. 1 [Que. 1(B)]

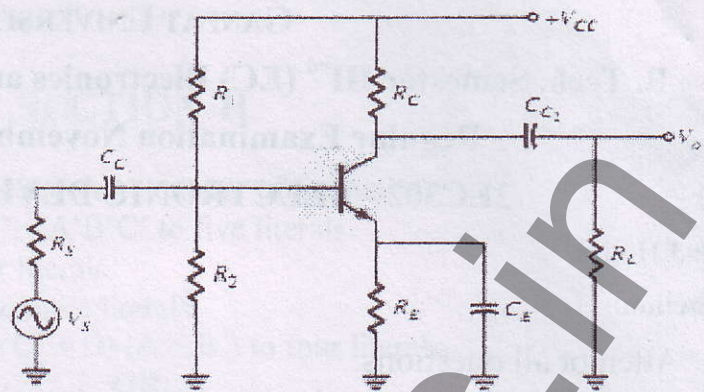


Figure. 2 [Que. 2(A)]

Section - II

- Que. - 4 (A) Describe charge storage phenomenon of normal p-n junction diode and how this phenomenon affects the operation of diode at high frequencies. 7
 (B) Determine I , V_1 , V_2 , and V_o for the series dc configuration of Figure 3. 5
- OR
- Que. - 4 (A) How static, dynamic and average resistance of diode is calculated? Explain in detail. 7
 (B) Determine the currents I_1 , I_2 , and I_{D2} for the network of Figure 4. 5
- Que. - 5 (A) Explain basic operation and characteristics of n-channel enhancement type MOSFET with neat and clean diagram. 6
 (B) What is the reason of cross-over distortion in class-B push pull power amplifier? Explain solution of it. 5
- OR
- Que. - 5 (A) Determine I_{DQ} and V_{DSQ} for the enhancement-type MOSFET of Figure 5. 6
 (B) Enlist the differences between Bipolar Junction Transistor and Field Effect Transistor. 5
- Que. - 6 (A) Write a short note on photolithography process of IC fabrication. 4
 (B) Determine the range of values of V_{in} that will maintain the Zener diode of Figure 6, in the "on" state. 4
 (C) Sketch a p-channel enhancement-type MOSFET with the proper biasing applied and indicate the channel, the direction of electron flow, and the resulting depletion region. 4

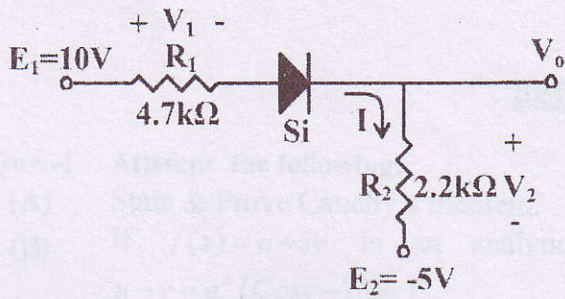


Figure. 3 [Que: 4(B)]

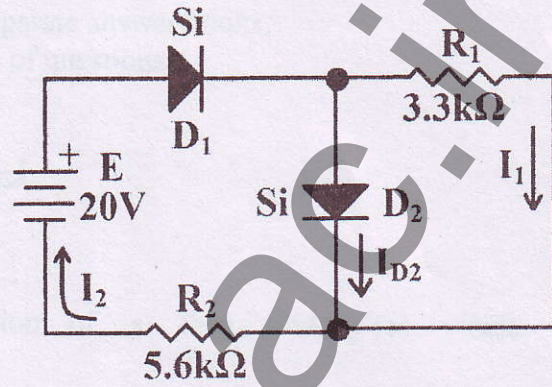


Figure. 4 [Que: 4(B)]

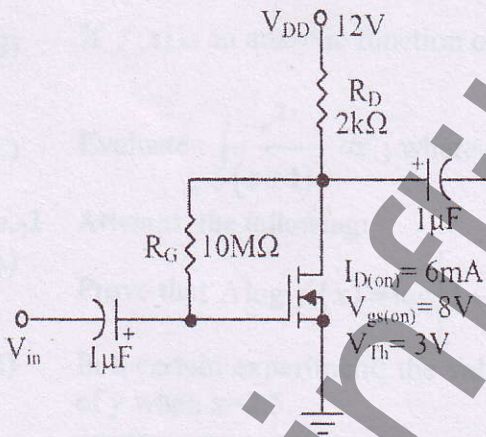


Figure. 5 [Que: 5(A)]

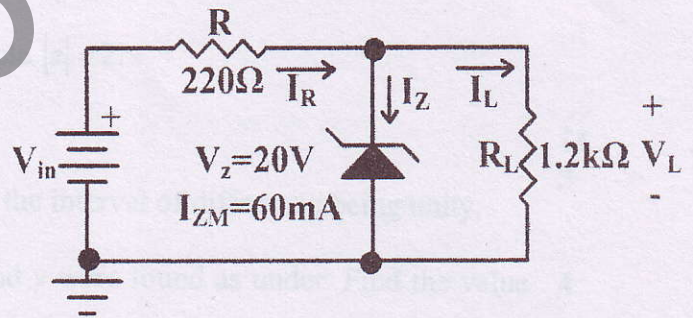


Figure. 6 [Que: 6(B)]

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